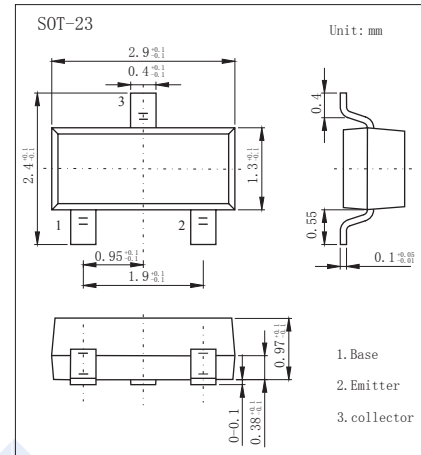


PNP Transistors

2SB710

■ Features

- Collector Current Capability $I_c = -0.5A$
- Collector Emitter Voltage $V_{CE0} = -25V$
- Complementary to 2SD602



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-30	V
Collector - Emitter Voltage	V_{CE0}	-25	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_c	-0.5	A
Collector Current - Pulse	I_{CP}	-1	
Collector Power Dissipation	P_c	200	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = -100 \mu A, I_E = 0$	-30			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = -10 mA, I_B = 0$	-25			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu A, I_c = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -20 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5V, I_c = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -300mA, I_B = -30mA$			-0.6	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -300mA, I_B = -30mA$			-1.5	
DC current gain	h_{FE}	$V_{CE} = -10V, I_c = -150mA$	85		340	
		$V_{CE} = -10V, I_c = -500mA$	40			
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			15	pF
Transition frequency	f_T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		200		MHz

■ Classification of $h_{FE}(1)$

Type		2SB710-Q	2SB710-R	2SB710-S
Range	85-340	85-170	120-240	170-340
Marking	C	CQ	CR	CS

PNP Transistors

2SB710

■ Typical Characteristics

